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**1N6263**  
**1N5711**

## Features

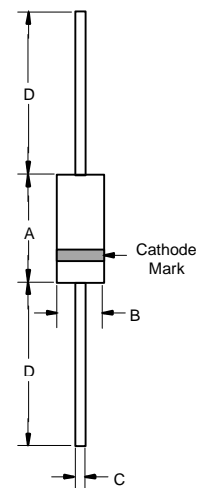
- High Reverse Breakdown Voltage
- Low Forward Voltage Drop
- For General Purpose Application

**400 mWatt Small  
Signal Schottky Diode  
60 to 70 Volts**

## Maximum Ratings

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Maximum Thermal Resistance; 300°C/W Junction To Ambient

DO-35



Electrical Characteristics @ 25°C Unless Otherwise Specified

|   |             |               |  |
|---|-------------|---------------|--|
| Peak Reverse Voltage                                    | $V_{RRM}$   | 60V<br>70V    |  |
| Minimum Reverse Breakdown Voltage                       | $V_{(BR)R}$ | 60V<br>70V    | $I_R = 10\mu A$                                |
| Power Dissipation                                       | $P_{TOT}$   | 400mW         | Infinite Heat sink                             |
| Junction Temperature                                    | $T_J$       | 125°C         |  |
| Peak Forward Surge Current                              | $I_{FSM}$   | 2.0A          | Single cycle surge 10μs square wave            |
| Maximum Instantaneous Forward Voltage                   | $V_F$       | 0.41V<br>1.0V | $I_{FM} = 1.0mA$ ;<br>$I_{FM} = 15mA$          |
| Maximum DC Reverse Current At Rated DC Blocking Voltage | $I_R$       | 200nA         | $V_R = 50Volts$<br>$T_J = 25^\circ C$          |
| Typical Junction Capacitance                            | $C_J$       | 2pF           | Measured at 1.0MHz, $V_R = 0V$                 |
| Reverse Recovery Time                                   | $T_{rr}$    | 1.0nS         | $I_F = 5mA$<br>$V_R = 6V$<br>$R_i = 100\Omega$ |

| DIM | INCHES |      | MM    |      | NOTE |
|-----|--------|------|-------|------|------|
|     | MIN    | MAX  | MIN   | MAX  |      |
| A   | ---    | .166 | ---   | 4.2  |      |
| B   | ---    | .079 | ---   | 2.00 |      |
| C   | ---    | .020 | ---   | .52  |      |
| D   | 1.000  | ---  | 25.40 | ---  |      |

Note: Valid provided that leads at a distance of 4mm from case are kept ambient temperature.

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Fig.1 Typical variation of fwd. current vs forward. voltage for primary conduction through the Schottky barrier

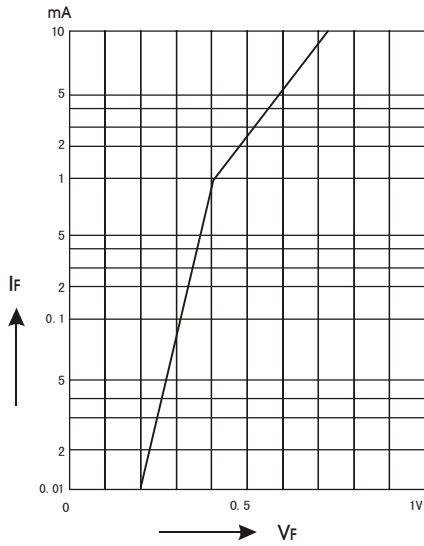


Fig.2 Typical forward conduction curve of combination Schottky barrier and PN junction guard ring

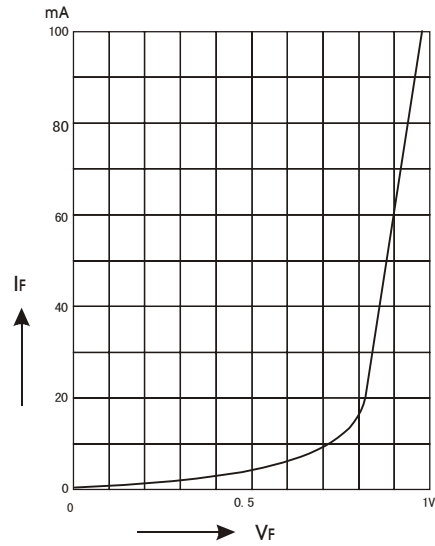


Fig.3 Typical variation of reverse current at various temperatures

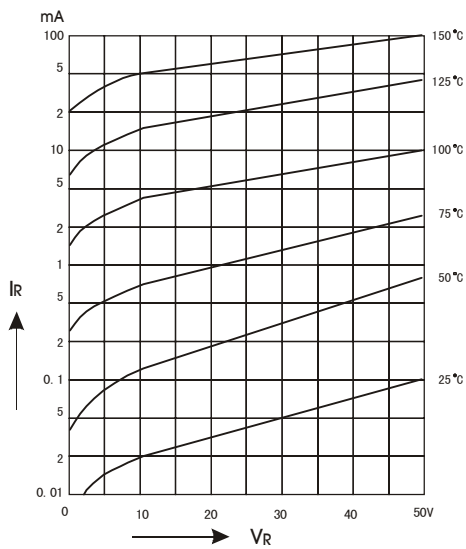


Fig.4 Typical capacitance curve as a function of reverse voltage

